

Appl. No. 09/833,711
Amdt. dated Oct 12, 2005
Reply to Notice of Sep 29, 2005

treatment at about 800°C to minimize the presence of Si-O_x-H_y-N_z compounds after said low-temperature treatment.

22.(currently amended) A method as claimed in claim 21, wherein said silica film is deposited in a vacuum chamber whose pressure is maintained by a vacuum pump having a controllable pumping speed, and said total gas-deposition pressure is maintained by controlling said pumping speed.

23.(currently amended) A method as claimed in claim 21, wherein said silica film is deposited at a temperature of about 400°C.

24.(previously presented). A method as claimed in claim 21, wherein said silicon-containing gas is SiH₄, said oxygen-containing gas is N₂O, and said carrier gas is N₂.

25.(canceled)

26. (canceled)

27. (canceled)